

SUBSTRATE PROCESSING APPARATUS AND SUBSTRATE
PROCESSING METHOD

ABSTRACT

5 To provide a substrate processing apparatus and a
substrate processing method capable of stably
generating plasma under a low pressure.

 A substrate processing apparatus is configured to
repeat a step of supplying the source RF signal to the
10 upper electrode to generate plasma in the plasma
processing chamber in a state in which a magnetic field
is generated by the electromagnet in the plasma
processing chamber and depositing a deposit on the
substrate; and a step of supplying the source RF signal
15 to the upper electrode to generate plasma in the plasma
processing chamber in a state in which a magnetic field
is generated by the electromagnet in the plasma
processing chamber and etching the substrate, wherein
a power level of the source RF signal in the step of
20 etching the substrate is lower than a power level of
the source RF signal in the step of depositing the
deposit on the substrate.

[Fig. 4]